



# PSMN2R9-100SSE

N-channel 100 V, 2.9 mOhm MOSFET with enhanced SOA in LFPAK88

3 July 2024

Product data sheet

## 1. General description

N-channel enhancement mode MOSFET in a LFPAK88 package qualified to 175 °C. Part of Nexperia's Application Specific MOSFETs (ASFETs) for Hotswap and Soft Start. The PSMN2R9-100SSE delivers very low  $R_{DSon}$  and enhanced safe operating area performance in a high-reliability copper-clip LFPAK88 package.

PSMN2R9-100SSE complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn-on, low  $R_{DSon}$  to minimize  $I^2R$  losses and deliver optimum efficiency when turned fully ON.

## 2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Low  $R_{DSon}$  for low  $I^2R$  conduction losses
- LFPAK88 package for applications that demand the highest performance and reliability

## 3. Applications

- Hot swap
- Load switch
- Soft start
- E-fuse
- Telecommunication systems based on a 48 V backplane/supply rail

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	-	210	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	341	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	-	2.3	2.9	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 100\text{ °C}$ ; <a href="#">Fig. 13</a>	-	3.4	4.6	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 50\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	6.4	21.3	49	nC
$Q_{G(tot)}$	total gate charge		63	125	188	nC

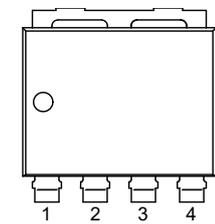
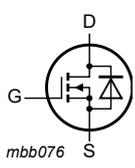
N-channel 100 V, 2.9 mOhm MOSFET with enhanced SOA in LFAK88

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 71\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped; $t_p = 124\ \mu\text{s}$ ; <a href="#">Fig. 4</a>	[1]	-	-	575 mJ
<b>Source-drain diode</b>						
$Q_r$	recovered charge	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 18</a>	-	57	-	nC

[1] Protected by 100% test

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>LFAK88 (SOT1235)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R9-100SSE	LFAK88	plastic, single-ended surface-mounted package (LFAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R9-100SSE	X2E9S10S

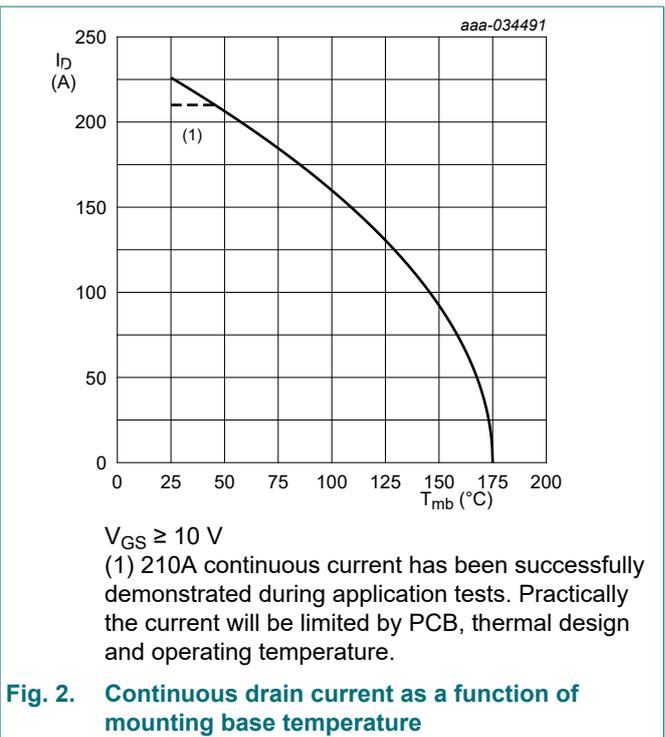
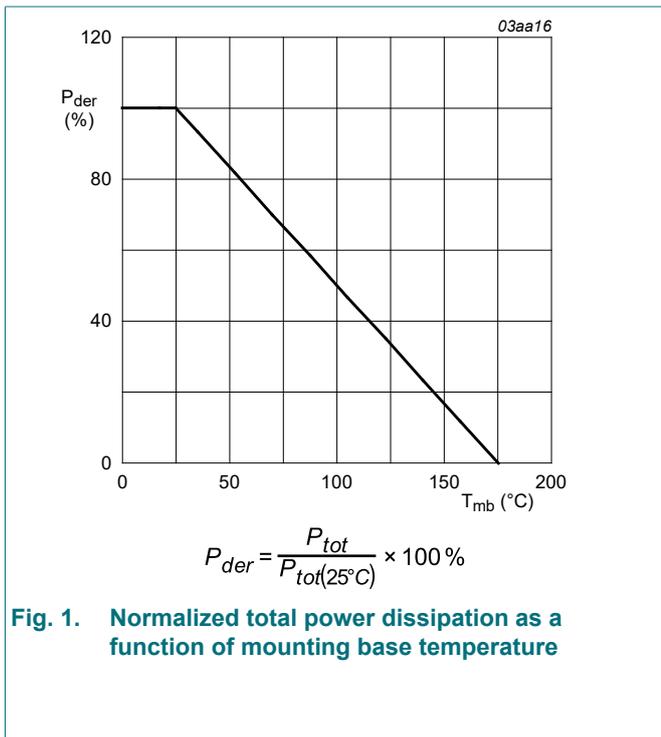
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).  $T_j = 25\text{ °C}$  unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	341	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	210	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>	-	160	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>	-	904	A
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	210	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	904	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 71\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; $t_p = 124\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a>	[1]	-	575 mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} \leq 100\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $R_{GS} = 50\text{ }\Omega$ ; <a href="#">Fig. 4</a>	[1]	-	71 A

[1] Protected by 100% test



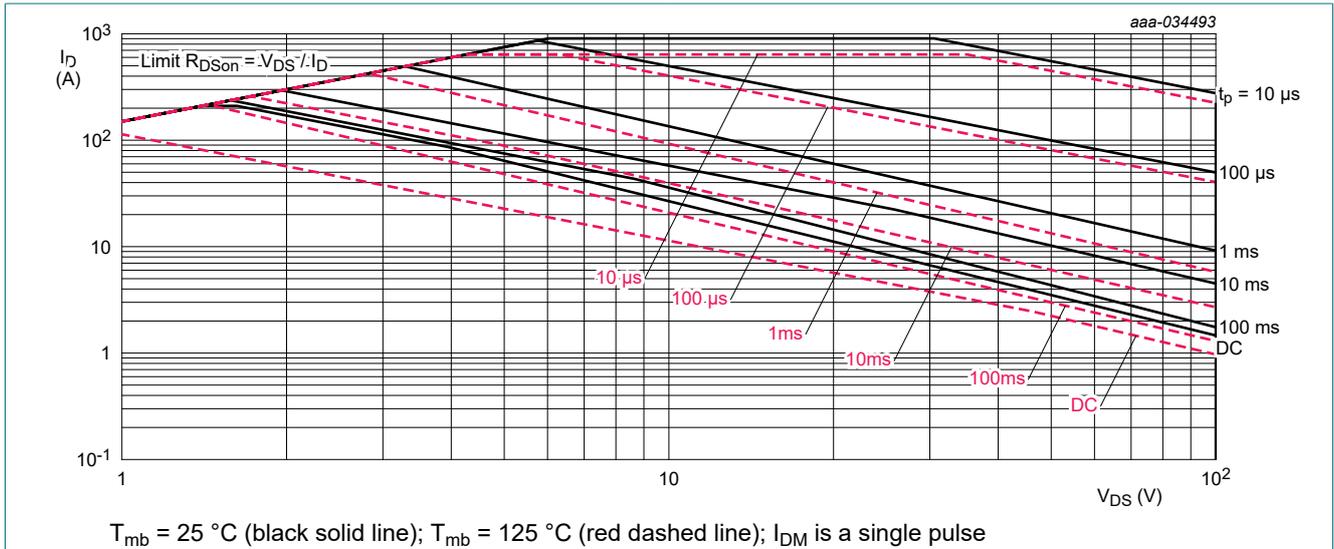


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

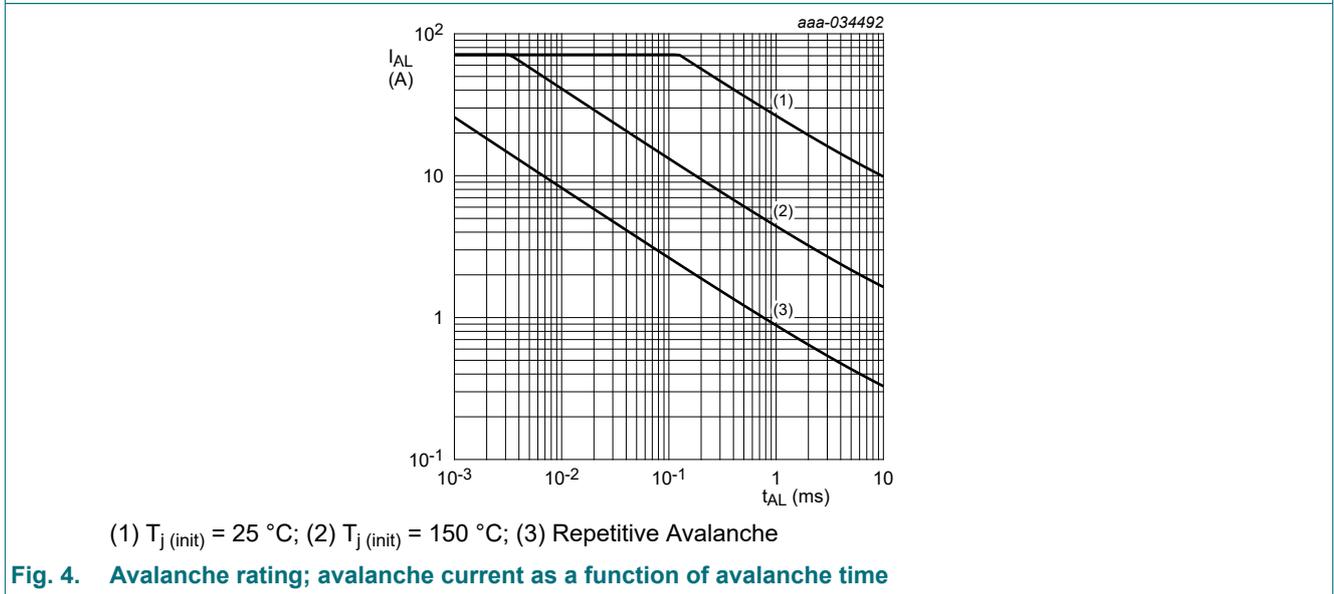


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	0.24	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	<a href="#">Fig. 6</a>	-	35	-	K/W
		<a href="#">Fig. 7</a>	-	70	-	K/W

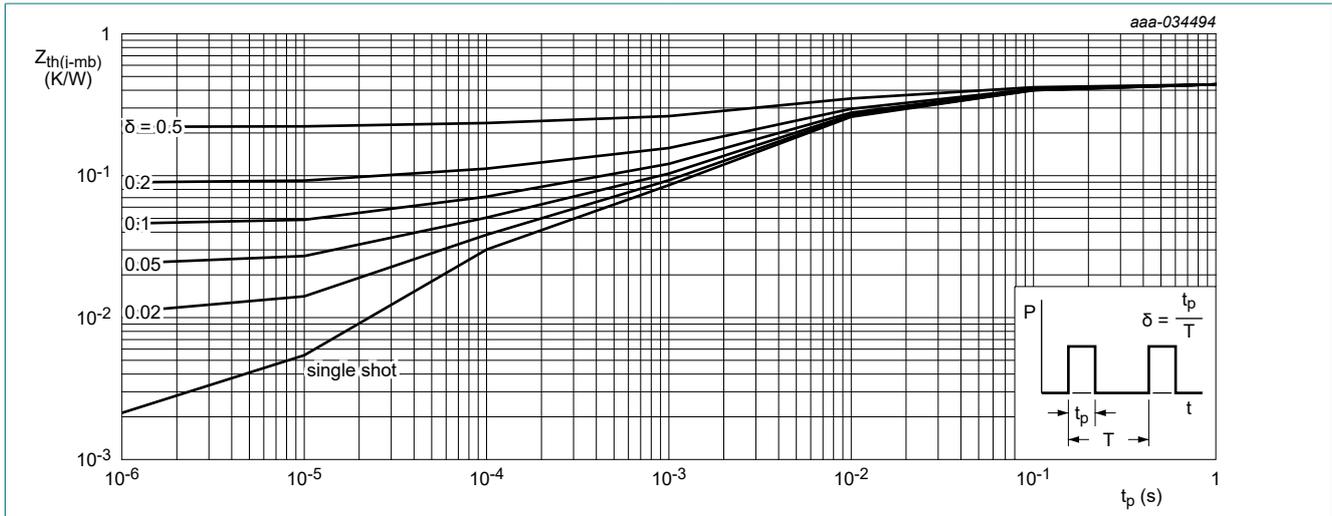
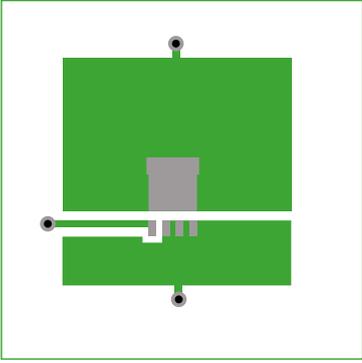
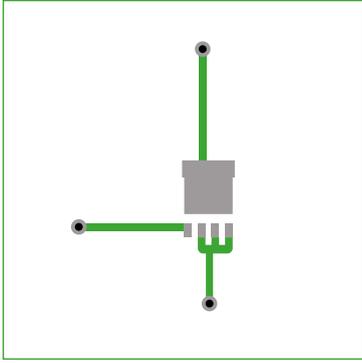


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

 <p>aaa-029383</p> <p>Copper square 25.4 mm square; 70 μm thick on FR4 board</p> <p>Fig. 6. PCB layout for thermal resistance from junction to ambient</p>	 <p>aaa-029384</p> <p>70 μm thick copper on FR4 board</p> <p>Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient</p>
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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	2	2.6	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ\text{C}$	-	1.6	-	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ\text{C}$	-	3	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ\text{C} \leq T_j \leq 150 \text{ }^\circ\text{C}$	-	-6.6	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.13	1	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	50	100	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 12</a>	-	2.3	2.9	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ <a href="#">Fig. 13</a>	-	3.4	4.6	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ <a href="#">Fig. 13</a>	-	4.8	6.7	m $\Omega$
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$	0.55	1.1	2.2	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 14; Fig. 15</a>	63	125	188	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 14; Fig. 15</a>	-	65	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 14; Fig. 15</a>	26	44	61	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 14; Fig. 15</a>	-	26.4	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	17.4	-	nC
$Q_{GD}$	gate-drain charge		6.4	21.3	49	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 14; Fig. 15</a>	-	4.9	-	V
$C_{iss}$	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 0.5 \text{ MHz};$ <a href="#">Fig. 16</a>	5679	9465	13250	pF
$C_{oss}$	output capacitance	$T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 16</a>	1427	2380	3806	pF
$C_{rss}$	reverse transfer capacitance		8	78	203	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 17</a>	-	31	-	ns
$t_r$	rise time	$R_{G(ext)} = 5 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	35	-	ns
$t_{d(off)}$	turn-off delay time		-	61	-	ns
$t_f$	fall time		-	43	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ <a href="#">Fig. 17</a>	-	0.79	1	V

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{rr}$	reverse recovery time	$I_S = 25 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	52	-	ns
$Q_r$	recovered charge	$V_{DS} = 50 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; Fig. 18	-	57	-	nC

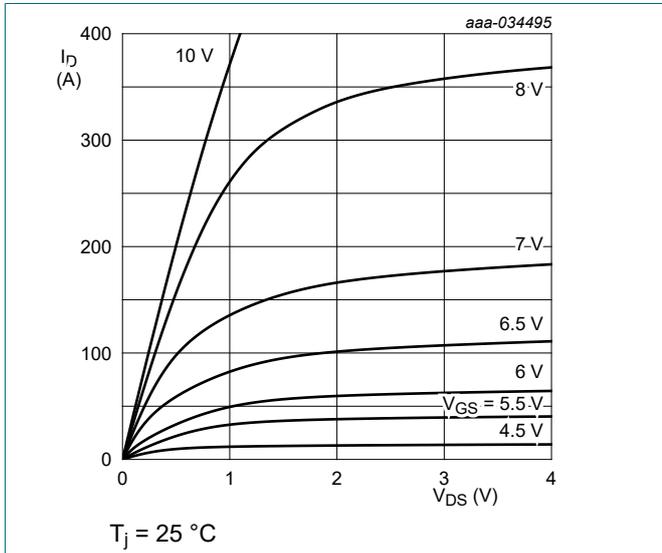


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

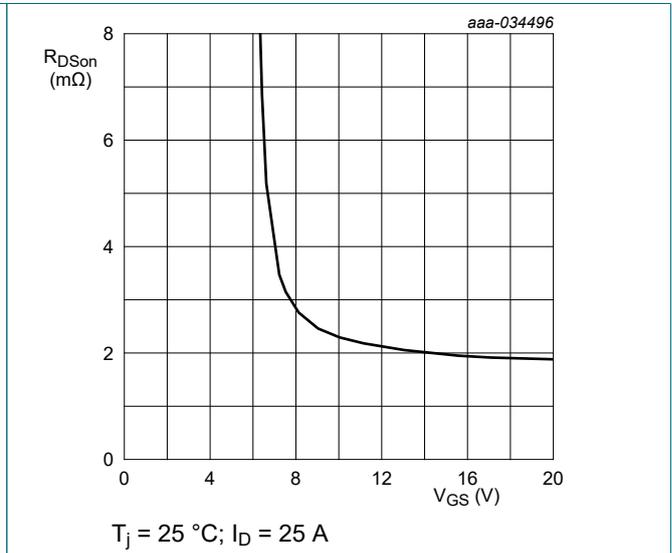


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

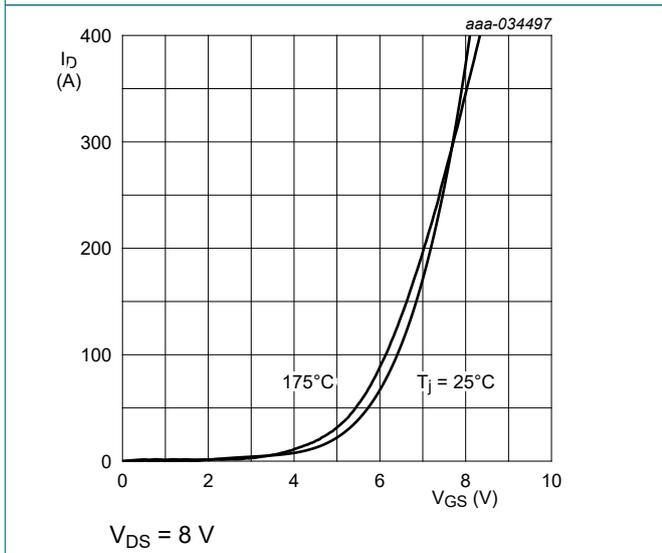


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

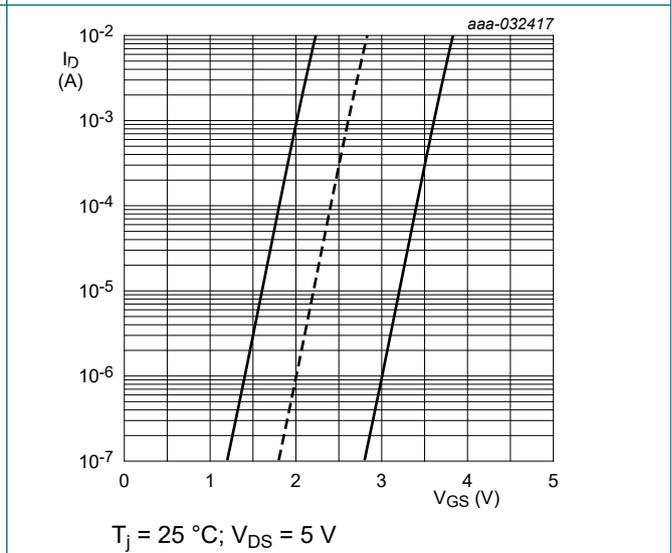


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

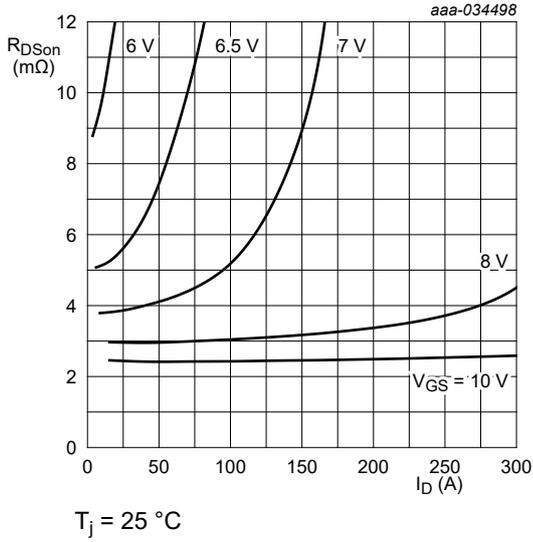
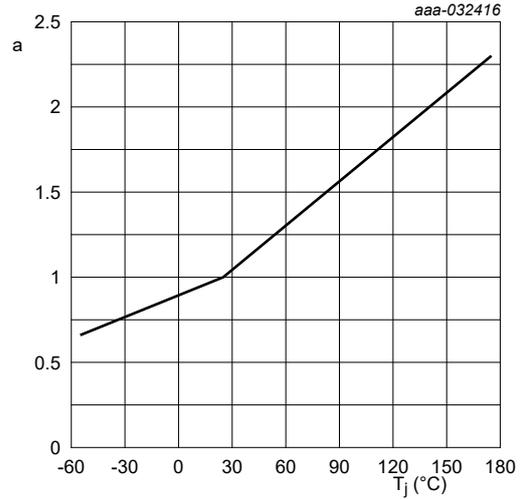


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ C)}$$

Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

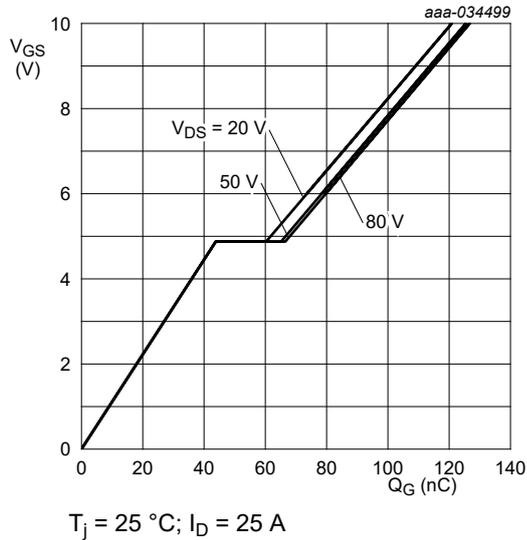


Fig. 14. Gate-source voltage as a function of gate charge; typical values

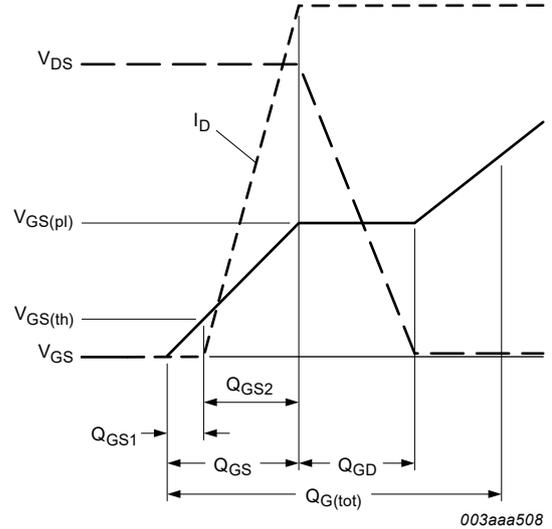


Fig. 15. Gate charge waveform definitions

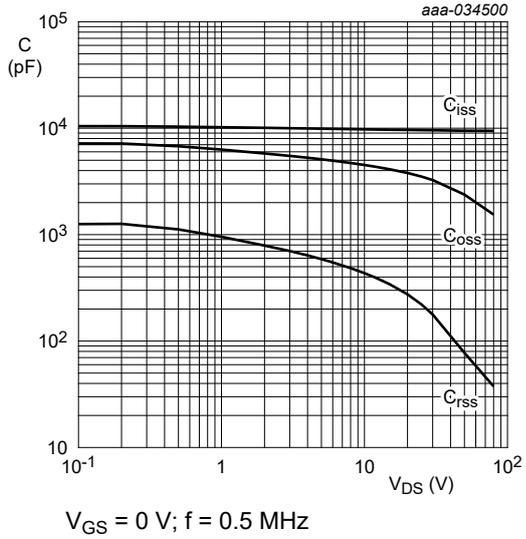


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

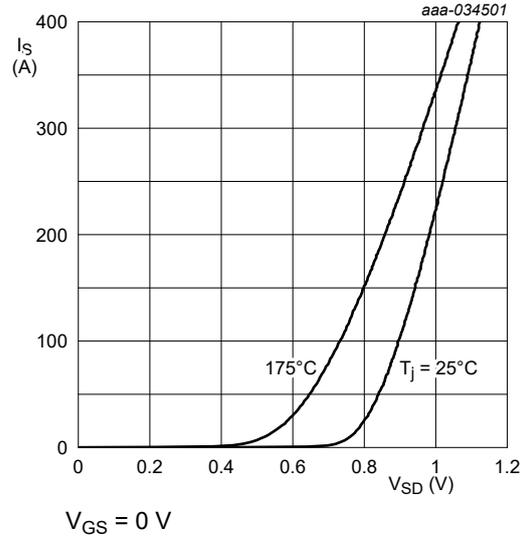


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

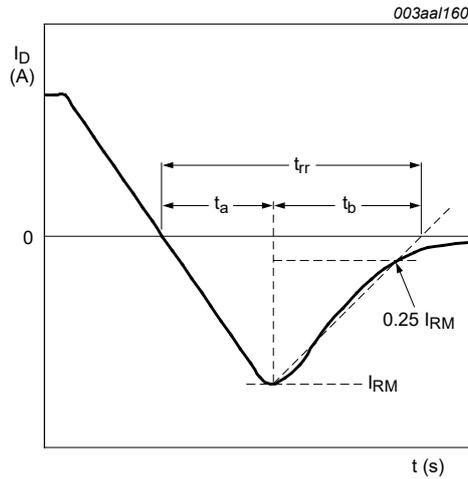


Fig. 18. Reverse recovery timing definition

### 11. Package outline

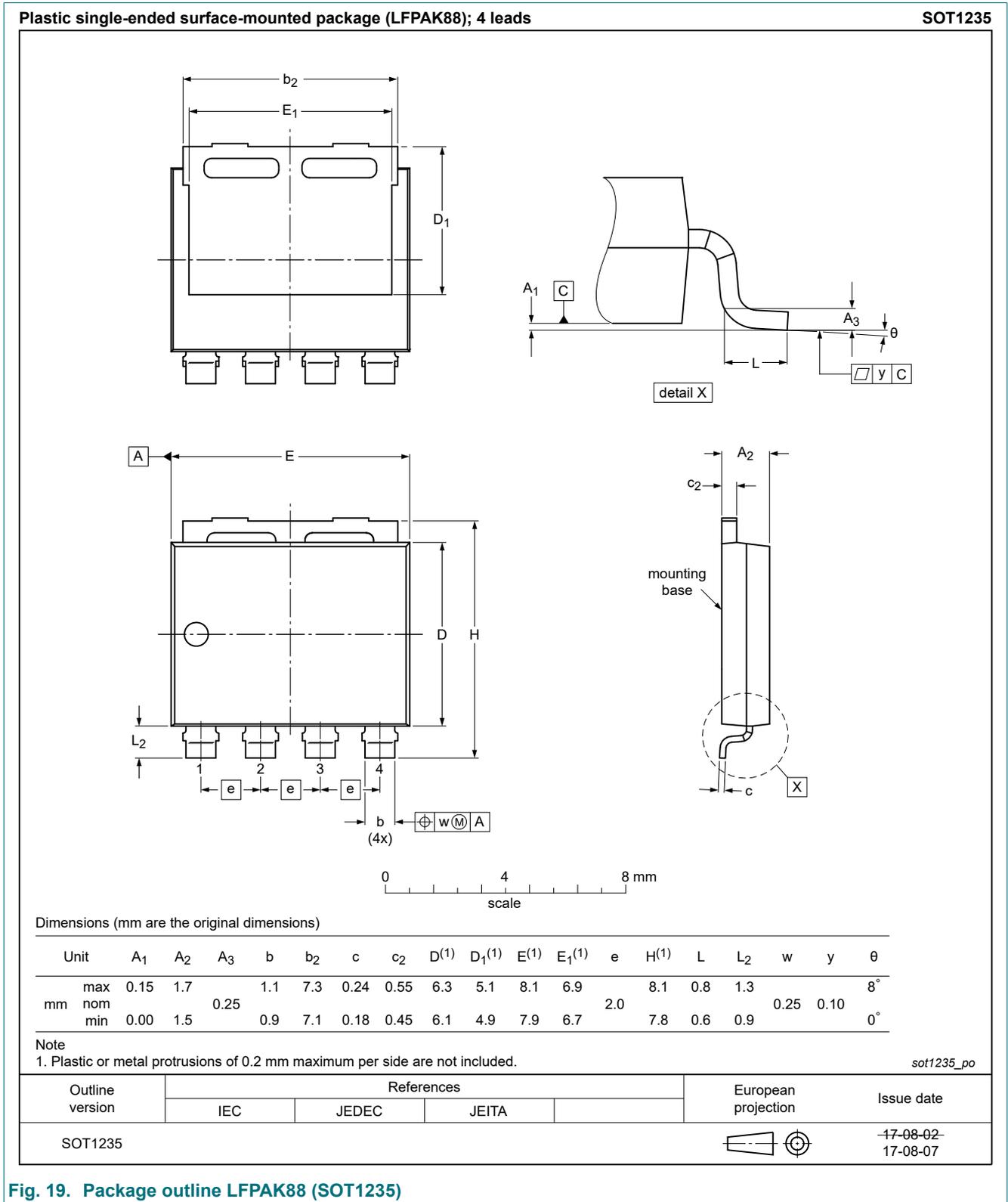
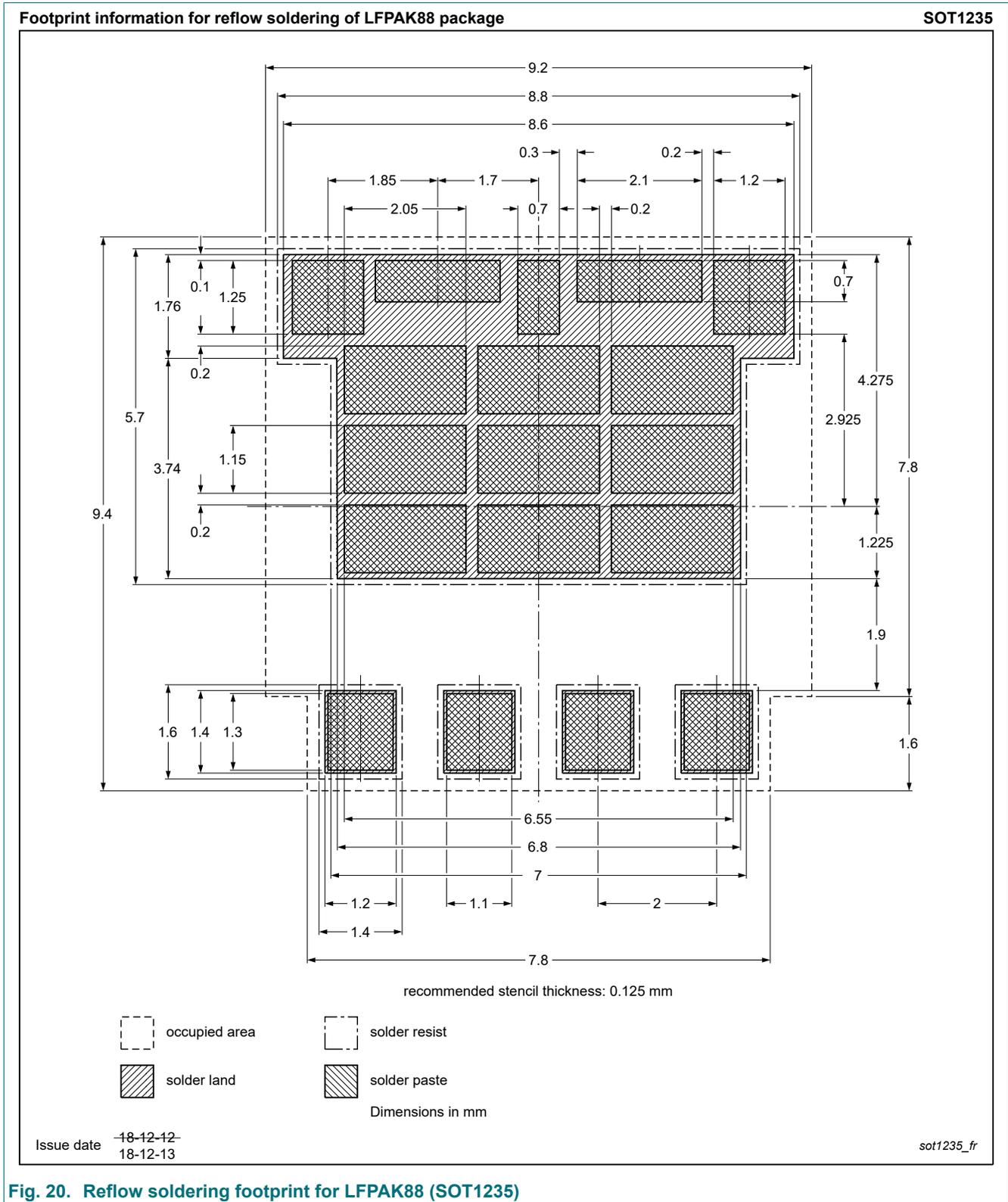


Fig. 19. Package outline LPAK88 (SOT1235)

## 12. Soldering



**Fig. 20. Reflow soldering footprint for LPAK88 (SOT1235)**

## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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